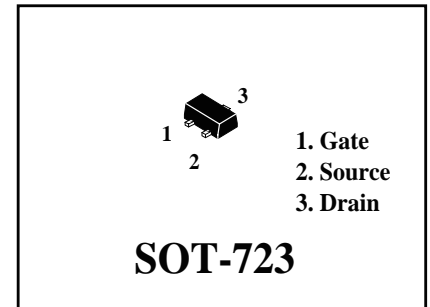


Surface Mount P-Channel MOSFET

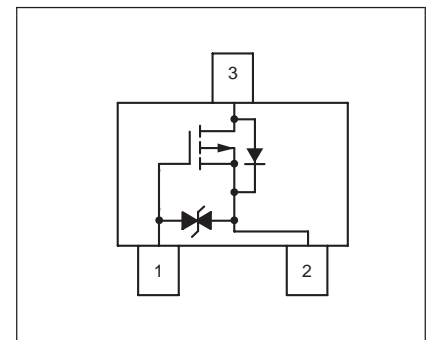
 Lead(Pb)-Free

Features:

- * Surface Mount Package
- * P-Channel Switch with Low $R_{DS(on)}$
- * Operated at Low Logic Level Gate Drive


Applications:

- * Load/Power Switching
- * Interfacing, Logic Switching
- * Battery Management for Ultra Small Portable Electronics


Maximum Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 6	V
Continuous Drain Current (note 1)	I_D	-0.66	A
Pulsed Drain Current ($t_p=10\mu\text{ s}$)	I_{DM}	-1.2	A
Power Dissipation (note 1)	P_D	150	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

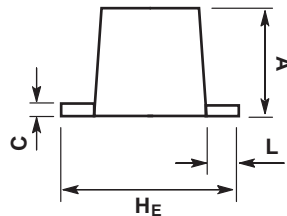
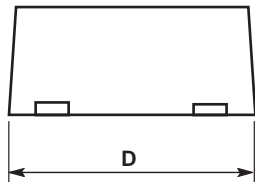
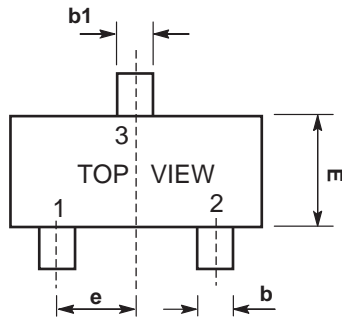
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			20	μA
Gate threshold voltage (note 2)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.35		-0.8	V
Drain-source on-resistance (note 2)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1A$			520	m Ω
		$V_{GS} = -2.5V, I_D = -0.8A$			700	m Ω
		$V_{GS} = -1.8V, I_D = -0.5A$			950	m Ω
Forward transconductance (note 2)	g_{FS}	$V_{DS} = -10V, I_D = -0.54A$		1.2		S
Diode forward voltage	V_{SD}	$I_S = -0.5A, V_{GS} = 0V$			-1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C_{iss}	$V_{DS} = -16V, V_{GS} = 0V, f = 1MHz$		113	170	pF
Output capacitance	C_{oss}			15	25	pF
Reverse transfer capacitance	C_{rss}			9	15	pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time (note 3)	$t_{d(on)}$	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_D = -200mA, R_{GEN} = 10\Omega$		9		ns
Turn-on rise time (note 3)	t_r			5.8		ns
Turn-off delay time (note 3)	$t_{d(off)}$			32.7		ns
Turn-off fall time (note 3)	t_f			20.3		ns

Notes :

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300 μs , Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producing.

SOT-723 Outline Demensions

Unit:mm



SOT-723			
Dim	Min	Nom	Max
A	0.45	0.50	0.55
b	0.15	0.20	0.27
b1	0.25	0.3	0.35
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H _E	1.15	1.20	1.25
L	0.15	0.20	0.25